In the Claims:

1-9 (canceled)

10. (previously presented) A method of fabricating a thin film resistor (TFR) structure comprising:

forming a TFR;

forming a dielectric layer over the TFR;

forming a first TFR via in the dielectric layer over a first end of the TFR and forming a second TFR via in the dielectric over a second end of the TFR;

forming a layer of titanium (Ti) over the first and second TFR vias; and

forming a layer of titanium nitride (TiN) on the (Ti) layer, the layer of Ti and the layer of TiN forming a first electrical interface portion to the first end of the TFR and a second electrical interface portion to the second end of the TFR.

11. (previously presented) The method of claim 10, the forming a first TFR via in the dielectric layer over a first end of the TFR and forming a second TFR via in the dielectric layer over a second end of the TFR comprising performing an etch process on the dielectric to form the first and second TFR vias.

12. (previously presented) The method of claim 10, wherein the dielectric layer is formed from a material selected from the group comprising: TEOS, silicon oxides and PEVCE silicon oxides.

13. (previously presented) The method of claim 10, the TFR formed from one of silicon chromium (SiCr) alloy, nickel chromium (NiCr) alloy, tantalum nitride, titanium nitride, and tungsten.

14. (previously presented) The method of claim 10, the TFR having a thickness in the range of about 90 ´ to about 400 ´.

15. (previously presented) The method of claim 10, the Ti layer having a thickness in the range from about 100 ´ to about 300 ´ and the TiN layer having a thickness in the range from about 800 ´ to about 3000 ´.

16. (previously presented) The method of claim 10, further comprising:

forming a dielectric material layer over the first electrical interface portion and the second electrical interface portion;

forming a first contact via extending to the first electrical interface portion and a second contact via extending to the second electrical interface portion;

filling the first contact via and the second contact via with a contact material; and

performing a chemical mechanical polish on the contact material to form a first contact portion and a second contact portion.

17. (previously presented) The method of claim 16, further comprising:

forming a dielectric material layer over the first contact portion and the second contact portion;

forming a first conductive via extending to the first contact portion and a second conductive via extending to the second contact portion;

filling the first conductive via and the second conductive via with a conductive material; and

performing an etch on the conductive material to provide a first conductive portion coupled to the first contact portion and a second conductive portion coupled to the second contact portion.

18. (previously presented) The method of claim 17, the contact material having at least one of tungsten, aluminum, aluminum alloy, copper, copper alloy and a tungsten alloy and the conductive material being at least one of aluminum, aluminum alloy, copper, copper alloy, tungsten, a tungsten alloy and a composite of predominantly aluminum with titanium and titanium nitride.

19. (previously presented) A method for forming a thin film resistor (TFR) structure, the method comprising:

forming a dielectric layer over a TFR layer;

etching the dielectric layer at least cone to form first TFR vias in the dielectric layer to form contact pads on a first end and a second end of the TFR layer;

sputter etching the dielectric layer and the TFR layer to remove any remaining oxide;

forming a layer of titanium (Ti) in the first TFR vias and over the oxide layer;

forming a layer of titanium nitride (TiN) on the (Ti) layer;

etching the titanium (Ti) layer and titanium nitride (TiN) layer to form an opening that defines a first electrical interface portion coupled to the first end of the TFR layer and a second electrical interface portion coupled to the second end of the TFR layer; and

forming a first contact coupled to the first electrical interface portion and a second contact coupled to the second electrical interface portion.

20. (previously presented) The method of claim 19, the Ti layer having a thickness in the range from about 100 ′ to about 300 ′ and the TiN la yer having a thickness in the range of from about 800 ′ to about 3000 ′.

21. (previously presented) The method of claim 19, the at least one etch of the dielectric layer to form the first TFR vias using a dilute hydrofluoric acid solution.